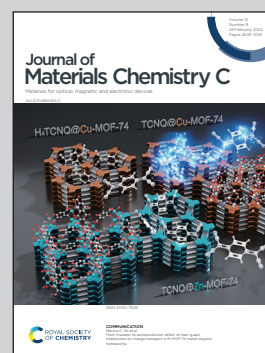


Showing research from Professor Cheol Seong Hwang's laboratory, Department of Materials Science and Engineering, Seoul National University, Seoul, Korea.

Improved electrical performance of ultra-thin $\text{Be}_x\text{Mg}_{1-x}\text{O}$ films using super-cycle atomic layer deposition

$\text{Be}_x\text{Mg}_{1-x}\text{O}$ dielectric films, deposited *via* super-cycle ALD with controlled sub-cycle ratios, exhibit a physical oxide thickness of 3.7 nm, equivalent oxide thickness of 1.3 nm, and low leakage, suitable for dynamic random access memory applications.

As featured in:



See Cheol Seong Hwang *et al.*,
J. Mater. Chem. C, 2024, **12**, 2714.